

1 16. (new) A semiconductor light-emitting device comprising:  
2 a substrate having a back surface provided with an  
3 n-type lower electrode;  
4 *E* a light-emitting layer provided on said substrate;  
5 a p-type semiconductor layer provided on said  
6 light-emitting layer; and  
7 an upper electrode provided on said p-type  
8 semiconductor layer;  
9 wherein said p-type semiconductor layer is a  
10 semiconductor layer selected from the group consisting of  
11 a ZnSe-based semiconductor layer, a ZnTe-based  
12 semiconductor layer and a BeTe-based semiconductor layer;  
13 and  
14 wherein said upper electrode includes an Au thin film  
15 positioned in contact with said p-type semiconductor layer  
16 and an n-type transparent conductor film formed on said Au  
17 thin film.

1 17. (new) The semiconductor light-emitting device according to  
2 claim 16, wherein said Au thin film has a thickness of 1 nm  
3 to 3 nm.  
*DI* *E*

1 18. (new) The semiconductor light-emitting device according to  
2 claim 16, wherein said n-type transparent conductor film is  
3 made of  $\text{In}_2\text{O}_3$  - 10 wt.% ZnO.

1 19. (new) The semiconductor light-emitting device according to  
2 claim 18, wherein said transparent conductor film of  $\text{In}_2\text{O}_3$  -  
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3        10 wt.% ZnO is formed by laser ablation and has  
4        characteristics as result from being formed by laser  
5        ablation.

1        20. (new) The semiconductor light-emitting device according to  
2        claim 16, wherein said Au thin film has a thickness of 2 nm  
3        to 3 nm and said n-type transparent conductor film is an  
4        *In<sub>2</sub>O<sub>3</sub> - 10 wt.% ZnO* layer having a thickness of 180 nm to  
5        200 nm.

1        21. (new) The semiconductor light-emitting device according to  
2        claim 16, wherein said n-type transparent conductor film  
3        has a multilayer structure including an upper layer and a  
4        lower layer, said lower layer having a flattened surface,  
5        and said upper layer having an uneven surface.

1        22. (new) The semiconductor light-emitting device according to  
2        claim 16, wherein said n-type transparent conductor film  
3        was deposited at room temperature and said device has  
4        characteristics as result from said n-type transparent  
5        conductor film having been deposited at room temperature.

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REMARKS:

1) All prior claims have been cancelled. New claims 16 to 22 have  
been submitted for examination in this Continued Prosecution  
Application. The new claims 16 to 22 are based on subject matter